	Type	Hits	Search Text	DBs
1	BRS	43	("chip on chip" or ((stack or stacked) with (semiconductor or IC or die or chip))) and (insulating or dielectric) near air	USPAT; JPO
2	BRS	6	257/777 and (insulating or dielectric) near air	USPAT; JPO
3	BRS	6	257/777 and (insulating or insulated or dielectric) near air	USPAT; JPO
4	BRS	19	(438/108 or 438/109 or 257/777 or 361/760) and (insulating or insulated or dielectric) near air	USPAT; JPO
5	BRS	191151	porous	USPAT; JPO
6	BRS	1856	porous near polymeric	USPAT; JPO
7	BRS	8	257/$.ccls. and porous near polymeric	USPAT; JPO
8	BRS	90	(438/108 or 438/109 or 257/777 or 361/760) and porous	USPAT; JPO
9	BRS	0	(438/108 or 438/109 or 257/777 or 361/760) and porous with air near pore	USPAT; JPO
10	BRS	6	(438/108 or 438/109 or 257/777 or 361/760) and porous with air	USPAT; JPO
11	BRS	20	(438/108 or 438/109 or 257/777 or 361/760) and porous with (air or void or gas)	USPAT; JPO
12	BRS	21	(438/108 or 438/109 or 257/777 or 361/760) and porous with (air or void or gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	7	("chip on chip" or ((stack or stacked) with (semiconductor or IC or die or chip))) and (insulating or dielectric) with (porous with (air or void or gas))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	1	"5407860".PN.	USPAT
15	BRS	1	"5444015".PN.	USPAT

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1	2002/07/01 01:43
2	2002/07/01 00:50
3	2002/07/01 00:56
4	2002/07/01 01:04
5	2002/07/01 00:59
6	2002/07/01 01:00
7	2002/07/01 01:00
8	2002/07/01 01:26
9	2002/07/01 01:27
10	2002/07/01 01:33
11	2002/07/01 01:42
12	2002/07/01 01:42
13	2002/07/01 01:48
14	2002/07/01 01:46
15	2002/07/01 01:46

	Type	Hits	Search Text	DBs
16	BRS	1	"5510293".PN.	USPAT
17	BRS	1	"5559055".PN.	USPAT
18	BRS	921	("chip on chip" or ((stack or stacked) with (semiconductor or IC or die or chip))) and (insulating or dielectric) with (air or void or gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	66	("chip on chip" or ((stack or stacked) with (semiconductor or IC or die or chip))) and (insulating or dielectric) near (air or void or gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	1	"Re36475".PN.	USPAT
21	BRS	267	257/777 and insulating near layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	254	257/777 and insulating near layer	USPAT
23	BRS	33	257/777 and second near insulating near layer	USPAT
24	BRS	895	257/777 and (IC or integrated near circuit)	USPAT
25	BRS	3	5869880.pn. or 6162740.pn. or 6239496.pn.	USPAT
26	BRS	14499	("chip on chip" or "die on die" or (chip or die or IC or semiconductor) near mount$3 near (chip or die or Ic or semiconductor)) or ((chip or die or IC or semiconductor) near stack$3 near ((chip or die or Ic or semiconductor))) and ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)	USPAT

	Time Stamp
16	2002/07/01 01:47
17	2002/07/01 01:47
18	2002/07/01 02:20
19	2002/07/01 01:50
20	2002/07/01 02:03
21	2002/07/01 02:20
22	2002/07/01 02:24
23	2002/07/01 06:46
24	2002/07/01 09:35
25	2002/07/01 09:36
26	2003/01/02 16:22

	Type	Hits	Search Text	DBs
27	BRS	14352	("chip on chip" or "die on die" or (chip or die or IC or semiconductor) near mount$3 near (chip or die or Ic or semiconductor)) or ((chip or die or IC or semiconductor) near stack$3 near ((chip or die or Ic or semiconductor))) and ((insulat$3 or dielectric) near (layer or film)) with (air or gas)	USPAT
28	BRS	10235	("chip on chip" or "die on die" or (chip or die or IC or semiconductor near device) near mount$3 near (chip or die or Ic or semiconductor near device)) or ((chip or die or IC or semiconductor near device) near stack$3 near ((chip or die or Ic or semiconductor near device))) same ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)	USPAT
29	BRS	10227	("chip on chip" or "die on die" or (chip or die or IC or semiconductor near device) near mount$3 near (chip or die or Ic or semiconductor near device)) or ((chip or die or IC or semiconductor near device) near stack$3 near ((chip or die or Ic or semiconductor near device))) same ((insulat$3 or dielectric) near (layer or film)) with (air or gas)	USPAT

	Time Stamp
27	2003/01/02 16:21
28	2003/01/02 16:31
29	2003/01/02 16:30

	Type	Hits	Search Text	DBs
30	BRS	3083	(("chip on chip" or "die on die" or (chip or die or IC or semiconductor near device) near mount$3 near (chip or die or Ic or semiconductor near device)) or ((chip or die or IC or semiconductor near device) near stack$3 near ((chip or die or Ic or semiconductor near device))) same ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)) and 257/$.ccls.	USPAT
31	BRS	10231	("chip on chip" or "die on die" or (chip or die or IC or semiconductor near device) near mount$3 near (chip or die or Ic or semiconductor near device)) or ((chip or die or IC or semiconductor near device) near stack$3 near ((chip or die or Ic or semiconductor near device))) same between same ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)	USPAT
32	BRS	0	("chip on chip" or "die on die") same between same ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)	USPAT
33	BRS	0	("chip on chip" or "die on die") same ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)	USPAT

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30	2003/01/02 16:31
31	2003/01/02 16:37
32	2003/01/02 16:37
33	2003/01/02 17:01

	Type	Hits	Search Text	DBs
34	BRS	19	((chip or die or IC or semiconductor near device) near mount$3 near (chip or die or Ic or semiconductor near device) or (chip or die or IC or semiconductor near device) near stack$3 near (chip or die or Ic or semiconductor near device)) same between same ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)	USPAT
35	BRS	54	((chip or die or IC or semiconductor near device) near mount$3 near (chip or die or Ic or semiconductor near device) or (chip or die or IC or semiconductor near device) near stack$3 near (chip or die or Ic or semiconductor near device)) same ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)	USPAT
36	BRS	0	("chip on chip" or "die on die") and ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)	USPAT
37	BRS	165	257/777 and ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas)	USPAT
38	BRS	177	257/777 and ((insulat$3 or dielectric) near (layer or film)) with (air or hole or gas or voids or gap or bubble)	USPAT
39	BRS	280	(257/777 or 361/760 or "chip on chip" or "die on die" or 257/686) and (insulat$3 or dielectric) with (air or gas or voids or gap or bubble)	USPAT

	Time Stamp
34	2003/01/02 16:46
35	2003/01/02 16:50
36	2003/01/02 17:02
37	2003/01/02 17:39
38	2003/01/02 17:45
39	2003/01/02 19:00

	Type	Hits	Search Text	DBs
40	BRS	10	(257/777 or 361/760 or "chip on chip" or "die on die" or 257/686) and (insulat$3 or dielectric) with (air or gas or voids or gap or bubble) with (decreas$3 or reduc$3) with dielectric near constant	USPAT
41	BRS	0	6077792.pn. and (insulat$3 or dielectric) with (air or gas or voids or gap or bubble) with (decreas$3 or reduc$3) with dielectric near constant	USPAT
42	BRS	0	6077792.pn. and (insulat$3 or dielectric) with (air or gas or voids or gap or bubble) same (decreas$3 or reduc$3) with dielectric near constant	USPAT
43	BRS	1	6333556.pn. and (insulat$3 or dielectric) with (air or gas or voids or gap or bubble) same (decreas$3 or reduc$3) with dielectric near constant	USPAT
44	BRS	23	(257/777 or 361/760 or "chip on chip" or "die on die" or 257/686) and (insulat$3 or dielectric) with (air or gas or voids or gap or bubble)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
45	BRS	111	(438/108 or 438/109) and (insulat$3 or dielectric) with (air or gas or voids or gap or bubble)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
46	BRS	1	"5128746".PN.	USPAT
47	BRS	1	"5289631".PN.	USPAT
48	BRS	1	"5471092".PN.	USPAT
49	BRS	1	"5634268".PN.	USPAT
50	BRS	1	"5665996".PN.	USPAT

	Time Stamp
40	2003/01/02 18:52
41	2003/01/02 18:53
42	2003/01/02 18:54
43	2003/01/02 18:54
44	2003/01/02 19:33
45	2003/01/02 19:33
46	2003/01/02 19:25
47	2003/01/02 19:25
48	2003/01/02 19:25
49	2003/01/02 19:25
50	2003/01/02 19:25

	Type	Hits	Search Text	DBs
51	BRS	64	(257/777 or 361/760 or "chip on chip" or "die on die" or 257/686 or 438/108 or 438/109) and (insulat$3 or dielectric) same (glue or adhesive) with (air or gas or voids or gap or bubble)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
52	BRS	68	(257/777 or 361/760 or "chip on chip" or "die on die" or 257/686 or 438/108 or 438/109) and (insulat$3 or dielectric or "non-conductive") same (glue or adhesive) with (air or gas or voids	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
53	BRS	69	(257/777 or 361/760 or "chip on chip" or "die on die" or 257/686 or 438/108 or 438/109) and (insulat$3 or dielectric or "non-conductive") same (glue or adhesive) with (air or gas or voids or gap or bubble or pores)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
54	BRS	414	(257/777 or 361/760 or "chip on chip" or "die on die" or 257/686 or 438/108 or 438/109) and (insulat$3 or dielectric or "non-conductive") with (air or gas or voids or gap or bubble or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
55	BRS	251	(257/777 or 361/760 or "chip on chip" or "die on die" or 257/686 or 438/108 or 438/109) and (insulat$3 or dielectric or "non-conductive") with (air or gas or voids or bubble or pores)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp
51	2003/01/02 19:55
52	2003/01/02 19:59
53	2003/01/02 20:01
54	2003/01/02 20:04
55	2003/01/02 20:04

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	144	(438/108 or 438/109 or 257/777 or 361/760 or 257/686) and porous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 16:26
2	BRS	209	(438/108 or 438/109 or 257/777 or 361/760 or 257/686 or 257/701) and air with (insulat$3 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 16:27
3	BRS	24	L2 and air with (within or inside) with (insulat$3 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 16:29

	Type	Hits	Search Text	DBs	Time Stamp
4	BRS	1411	(semiconductor or die or chip or IC) and air with (within or inside) with (insulat$3 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 17:09
5	BRS	2181	(semiconductor or die or chip or IC) and gas with (within or inside) with (insulat$3 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 17:10
6	BRS	27565	L5 gas near bubble	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 17:10

	Type	Hits	Search Text	DBs	Time Stamp
7	BRS	49	L5 and gas near bubble	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/02 17:10
8	BRS	1	"4667008".PN.	USPAT	2003/07/02 17:13
9	BRS	1	"4675577".PN.	USPAT	2003/07/02 17:13
10	BRS	1	"4866351".PN.	USPAT	2003/07/02 17:13
11	BRS	1	"5041762".PN.	USPAT	2003/07/02 17:13
12	BRS	1	"5326298".PN.	USPAT	2003/07/02 17:13
13	BRS	1	"4866351".PN.	USPAT	2003/07/02 17:15
14	BRS	1	"5041762".PN.	USPAT	2003/07/02 17:15
15	BRS	1	"5326298".PN.	USPAT	2003/07/02 17:15
16	BRS	1	"5382879".PN.	USPAT	2003/07/02 17:15
17	BRS	1	"5461279".PN.	USPAT	2003/07/02 17:16
18	BRS	1	"5469020".PN.	USPAT	2003/07/02 17:16